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Silicon PNP Epitaxial

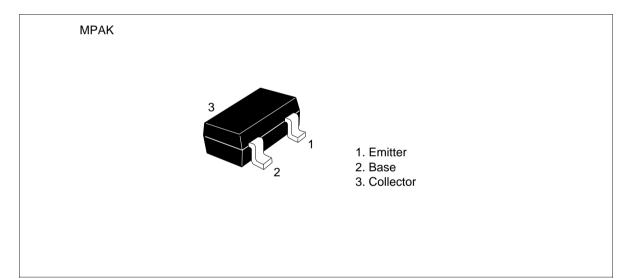


ADE-208-1008 (Z) 1st. Edition Mar. 2001

Application

- Low frequency amplifier
- Complementary pair with 2SC2618

Outline



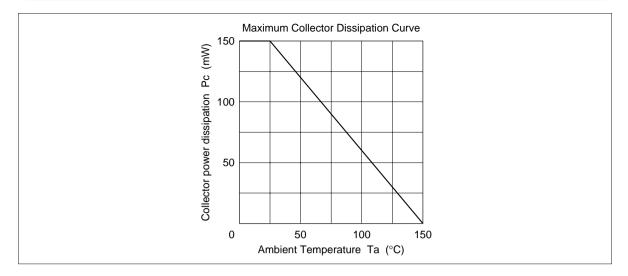
Absolute Maximum Ratings (Ta = 25° C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-35	V
Collector to emitter voltage	V _{CEO}	-35	V
Emitter to base voltage	V _{EBO}	-4	V
Collector current	l _c	-500	mA
Collector power dissipation	Pc	150	mW
Junction temperature	Тј	150	°C
Storage temperature	Tstg	–55 to +150	°C

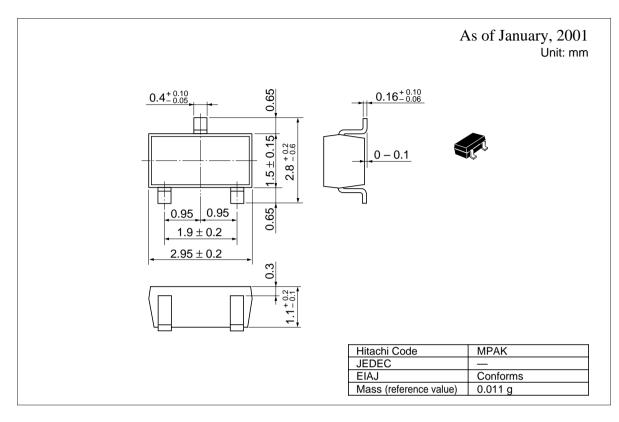
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	-35	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\rm (BR)CEO}$	-35	—	—	V	$I_c = -1$ mA, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	-4	_	_	V	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	—		-0.5	μΑ	$V_{\rm CB} = -20$ V, $I_{\rm E} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	-0.2	-0.6	V	$I_{c} = -150 \text{ mA}, I_{B} = -15 \text{ mA}$
DC current transfer ratio	h _{FE} *1	60	_	320		$V_{ce} = -3 \text{ V}, I_c = -10 \text{ mA}$
	h _{FE}	10	_	_		$V_{CE} = -3 \text{ V}, I_C = -500 \text{ mA}$ (Pulse test)
Base to emitter voltage	V _{BE}	_	-0.64	_	V	$V_{ce} = -3 \text{ V}, \text{ I}_{c} = -10 \text{ mA}$
Note: 1. The 2SA1121 is grouped by h _{FE} as follows.						
Grade B C	;	D				
Mark SB S	С	SD				
h _{FE} 60 to 120 1	00 to 200	160 to	320			

See characteristic curves of 2SA673.



Package Dimensions



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